

The Effects of Multiphase Formation on Strain Relaxation and Magnetization in Multiferroic BiFeO₃ Thin Films**

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Multiferroic epitaxial Bi-Fe-O thin films of different thicknesses (15–500 nm) were grown on SrTiO₃ (001) substrates by pulsed laser deposition under various oxygen partial pressures to investigate the microstructural evolution in the Bi-Fe-O system and its effect on misfit strain relaxation and on the magnetic properties of the films. Films grown at low oxygen partial pressure show the canted antiferromagnetic phase α -Fe₂O₃ embedded in a matrix of BiFeO₃. The ferromagnetic phase, γ -Fe₂O₃ is found to precipitate inside the α -Fe₂O₃ grains. The formation of these phases changes the magnetic properties of the films and the misfit strain relaxation mechanism. The multiphase films exhibit both highly strained and fully relaxed BiFeO₃ regions in the same film. The magnetization in the multiphase Bi-Fe-O films is controlled by the presence of the γ -Fe₂O₃ phase rather than heteroepitaxial strain as it is the case in pure single phase BiFeO₃. Also, our results show that this unique accommodation of misfit strain by the formation of α -Fe₂O₃ gives rise to significant enhancement of the piezo electric properties of BiFeO₃.

1. Introduction

Multiferroic materials simultaneously display ferroelectric and ferromagnetic properties in the same phase.^[1] In the 1960s to 1970s, these materials were first investigated to understand the magnetoelectric (ME) coupling effect.^[2,3] Recently, there is increased interest in multiferroic materials because of their potential applications in novel devices using the magnetoelectric effects including switching of the electric polarization controlled by an applied magnetic field.^[4–6] Very few intrinsic multiferroic compounds such as HoMnO₃ and TbMn₂O₅ exist in

nature or have been synthesized. Furthermore, these materials exhibit the ME coupling at low temperatures.^[6–9]

BiFeO₃ has attracted great attention because it is multiferroic well above room temperature.^[10,11] However, the small magnetization and narrow growth window of BiFeO₃ impede its use in practical applications. To enhance the magnetic and ferroelectric properties of BiFeO₃, chemical modification, and controlled stress through growth of heteroepitaxial films and variation in thickness have been attempted with varying degrees of success.^[5,12,13] In Bi-Fe-O, however, there are several phases of different structures, compositions, and electrical and magnetic properties which can co-exist. The presence of these phases can substantially affect the electrical and magnetic properties of the overall material. There has been a report on the coexistence of BiFeO₃ and γ -Fe₂O₃ phases in Bi-Fe-O films grown by pulsed laser deposition (PLD).^[14] We have recently reported on the coexistence of BiFeO₃ and Fe₂O₃ phases (α and γ) with a systematically varying degree of mixture controlled by the oxygen partial pressure during deposition.^[15] In the present work, we investigate the microstructural evolution in Bi-Fe-O films which form nanocomposites consisting of more than one phase when the thickness of the film is changed. We focus on characterization of the secondary phases and the effects of these phases on the relaxation of the lattice misfit strain and the magnetic properties of the overall films.

Figure 1a shows X-ray diffraction (XRD) spectra obtained from films of different thicknesses, t , grown at an oxygen partial pressure of 5 mTorr. Diffraction was performed using the ω -scan mode, and the intensities were integrated in χ between 85 and 95 degrees. The corresponding TEM cross-sectional images of some of the films are shown in Figure 1b. In our previous report,^[15] thin films of pure BiFeO₃, which has a perov-

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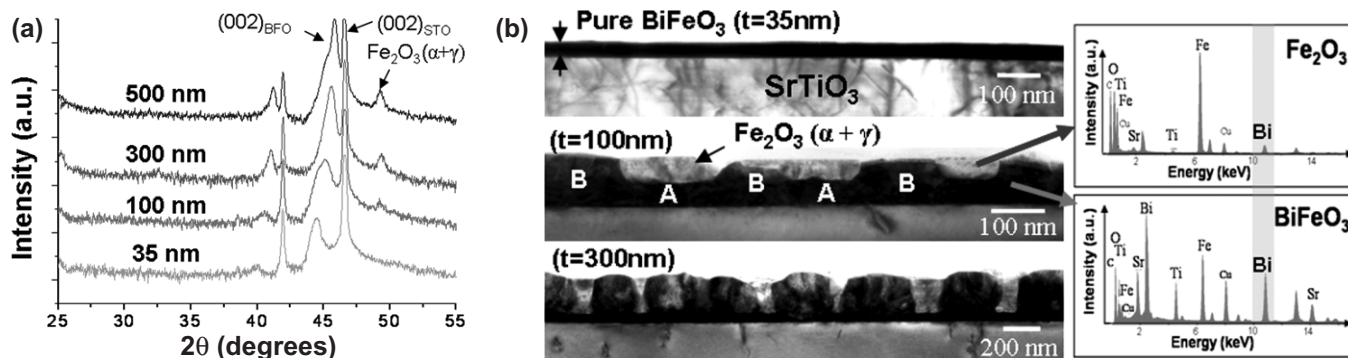


Figure 1. a) X-ray diffraction spectra (in log scale) and b) TEM cross-sectional images (left) and EDS spectra (right) of Bi-Fe-O films grown at 5 mTorr with different thickness. Nucleation of impurity phases starts at ~50 nm. The intensity of the peak labeled Fe₂O₃ in (a) corresponding to the impurity phase increases with increasing film thickness.

skite structure in bulk with $a = 0.395$ nm,^[16] grown at 20 mTorr and higher oxygen partial pressure showed a monoclinically distorted (by about 0.5°) tetragonal structure with the lattice constants, $a = 0.394$ nm, $c = 0.398$ nm. In the present work, the 35 nm thick film grown at 5 mTorr oxygen partial pressure shows the pure epitaxial BiFeO₃ phase with the [001] orientation and a slightly larger lattice parameter ($c = 0.407$ nm) than that of the pure 300 nm thick BiFeO₃ film grown at 20 mTorr. As the film thickness increases, the intensity of the (002) diffraction peaks of the BiFeO₃ increases, and the peak shifts to a higher 2θ angle (see Fig. 1a). This indicates that the out-of-plane lattice parameters of BiFeO₃ decreases with increasing thickness. We also observed peaks corresponding to the (024) plane of the α -Fe₂O₃ phase and the (240) plane of the γ -Fe₂O₃ phase. The α -Fe₂O₃ phase has a rhombohedral crystal structure (space group: R-3c) with lattice constants of $a = b = 0.505$ nm, $c = 1.319$ nm, and the γ -Fe₂O₃ phase has the cubic (or inverse spinel) crystal structure that belongs to the space group P4132 (or $Fd-3m$) with lattice parameters $a = 0.83515$ nm.^[17] The intensity of the peaks corresponding to α - and γ -Fe₂O₃ in Figure 1a increases with increasing film thickness.

From the TEM cross-sectional images of films with different thickness shown in Figure 1b, we can see that the secondary phase, α -Fe₂O₃, forms in the surface region of films with thickness of 50 nm, which grows to the surface of the film with continued deposition. The EDS spectra in Figure 1b obtained from the bright and dark columns of the film confirmed the chemical composition of the separated phases. The EDS spectrum from the bright columns shows little bismuth contents (5.5 at %), and the ratio between iron (38.5 at %) and oxygen (56 at %) is 1:1.45, which is consistent with Fe₂O₃. The EDS spectrum from the dark columns, shows a 1:1.1 ratio between bismuth (24 at %) and iron (26.3 at %), which is consistent with BiFeO₃.

The magnified TEM images from cross-sectional and plan-view specimens in Figure 2a show that the γ -Fe₂O₃ phase forms precipitates with a plate-like

shape embedded in the α -Fe₂O₃ regions. From indexing the SAD patterns (see Fig. 2b), we obtained the following preferred in-plane epitaxial relations among BiFeO₃, α -Fe₂O₃, and γ -Fe₂O₃: $[100]_{\text{BiFeO}_3} // [102]_{\alpha} // [120]_{\gamma}$, and $[010]_{\text{BiFeO}_3} // [1-12]_{\alpha} // [2-1-1]_{\gamma}$. The γ -Fe₂O₃ also showed different orientations with respect to BiFeO₃ and α -Fe₂O₃ in other areas of the sample. Typically, Fe₂O₃ has two different crystal structures. One is a spinel structure (maghemite, γ -Fe₂O₃) and the other is a corundum structure (hematite, α -Fe₂O₃). In bulk, it is known that there is an irreversible transformation from γ -Fe₂O₃ to α -Fe₂O₃ occurring at temperatures above 400 °C via restacking of the oxygen layers and displacement of the Fe ions located in the interstices rather than recrystallization.^[18] This transformation occurs on the close-packed planes of α - and γ -Fe₂O₃ without diffusion, and thus the crystal orientation relationship between α - and γ -Fe₂O₃ in the bulk was reported as $(0001)_{\alpha} // (111)_{\gamma}$, $[01-10]_{\alpha} // [1-10]_{\gamma}$.^[17,19,20] In our experiments, however, we observed the co-

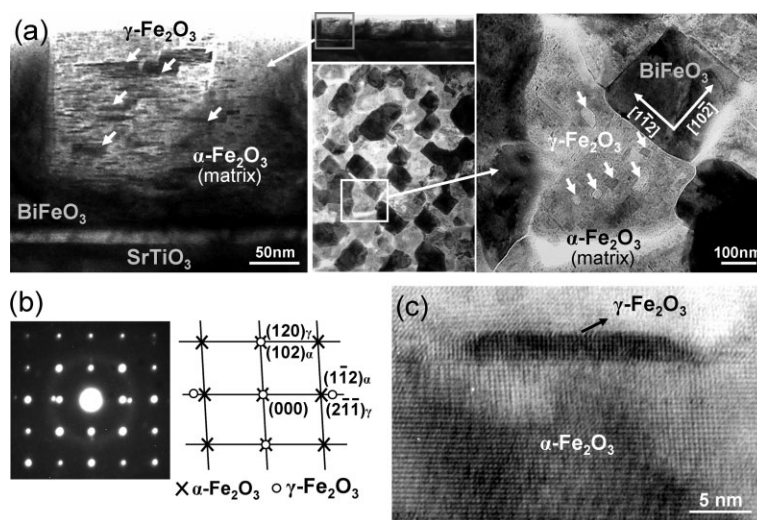


Figure 2. TEM bright field images and SAD pattern of bismuth iron oxide thin films fabricated on (001) SrTiO₃ substrates. a) Cross-section (left) and plan-view (right) images showing γ -Fe₂O₃ precipitates and b) SAD pattern and corresponding schematic of α -Fe₂O₃ and γ -Fe₂O₃ phases in the film deposited at 1 mTorr. c) High resolution cross sectional TEM image of γ -Fe₂O₃ in α -Fe₂O₃ matrix.

existence of α -Fe₂O₃ and γ -Fe₂O₃ in the film. Furthermore, the γ -Fe₂O₃ phase in the present study showed several different orientation relationships with α -Fe₂O₃. This is probably due to the fact that PLD is a non-equilibrium growth technique.

The SAD pattern and the schematic in Figure 2b are from one of the Fe₂O₃ regions where α -Fe₂O₃ and γ -Fe₂O₃ coexist. The out-of-plane and the in-plane parameters of α -Fe₂O₃ as measured from the SAD patterns were $d(102)=0.364$ nm and $d(1-12)=0.370$ nm, respectively. The out-of-plane and the in-plane parameters in γ -Fe₂O₃ as measured from a high resolution TEM image (see Fig. 2c) were $d(120)=0.37$ nm and $d(2-1-1)=0.34$ nm, respectively, which are in good agreement with published values (i.e., JCPDS #39-1346). The lattice mismatch between α - and γ -Fe₂O₃ is 8.1 %. A distortion of the α -Fe₂O₃ lattice and strain concentration around γ -Fe₂O₃ was observed due to the large lattice mismatch.

The existence of secondary phases can affect the relaxation of misfit strain in BiFeO₃ and result in significant change in the ferroelectric and ferromagnetic properties of the BiFeO₃ film. To compare the relaxation mechanism of the out-of-plane lattice parameter of multiphase Bi-Fe-O with pure BiFeO₃, Bi-Fe-O films with a gradual change in thickness were fabricated by the gradient deposition technique using a shadow mask. An oxygen partial pressure of 20 mTorr was selected to fabricate a pure BiFeO₃ film, and 5 mTorr to make a multiphase Bi-Fe-O film. The thickness of these films varied in the range of 30–300 nm for pure BiFeO₃ and 30–290 nm for the multiphase Bi-Fe-O film. Figure 3a and b show a superposition of X-ray microdiffraction scans from different regions of the pure BiFeO₃ film (Fig. 3a) and multiphase Bi-Fe-O film (Fig. 3b) with different thicknesses. In Figure 3a, the position of the (002) peak of BiFeO₃ was found to shift from $2\theta=44.6^\circ$ to 45.6° as the film thickness increases. In contrast, the spectra in Figure 3b show a broad peak at $2\theta\approx44.5^\circ$ in the thin regions of the sample which evolves into two peaks as the film thickness increases; the thicker regions show a peak at $\sim45.7^\circ$ which corresponds to BiFeO₃. However, a second peak at $\sim44.5^\circ$ remains with weaker intensity even for thickness up to 300 nm. The observation of two peaks in Figure 3b is consistent with the coexistence of a strained region and a relaxed region in the film. More evidence of the two regions was obtained from TEM images as shown below. These results indicate that the multiphase film has a different relaxation mechanism than the pure BiFeO₃ films. Typically, the misfit strain between a film and a substrate is relaxed by the generation of misfit dislocations at the interface with increasing film thickness. As shown in Figure 3a, pure BiFeO₃ showed typical relaxation mechanisms in which the strain gradually relaxes as the film thickness increases (see Fig. 3c). The region in the multiphase Bi-Fe-O film with small thickness showed a highly strained film as expected. However, the thicker region of the film showed both a

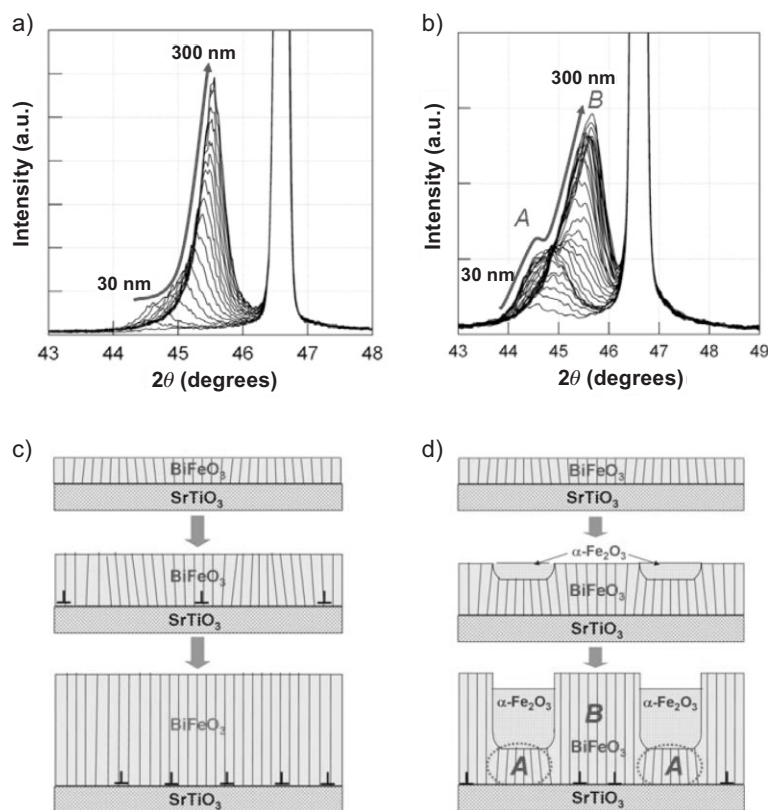


Figure 3. Superpositions of X-ray microdiffraction scans from regions of films with a thickness gradient grown at a) 20 mTorr and b) 5 mTorr. The thicknesses were varied from 30 to 300 nm. Schematics of the misfit strain relaxation mechanism in c) pure BiFeO₃ film and d) multiphase Bi-Fe-O film are suggested. Multiphase film shows coexistence of highly strained region (A) and relaxed region (B).

relaxed region (represented by the X-ray “peaks” labeled B in Figure 3b and a highly strained region (labeled A in Fig. 3b) in the film even though the thickness of the film was above the critical thickness for relaxation to take place. This observation can be explained by the formation of α -Fe₂O₃ regions, which appeared in the surface region of the film with thickness ≥ 50 nm. The transformation to α -Fe₂O₃ in the surface region of the film reduces the thickness of the BiFeO₃ underneath. Therefore, the area below α -Fe₂O₃ (marked A in Fig. 1b) showed higher misfit in-plane strain and a lower misfit dislocation density than the region with pure BiFeO₃ surrounding the α -Fe₂O₃ columns (marked B in Fig. 1b) as determined by high resolution TEM images (not shown). The formation of α -Fe₂O₃ regions enhances the relaxation of in-plane misfit strain in the BiFeO₃ columns between α -Fe₂O₃ columns due to the reduction in volume (calculated below). The reduction of volume releases both the in-plane compressive strain and out-of plane tensile strain in the BiFeO₃ regions surrounding α -Fe₂O₃ (see Fig. 3d).

In order to determine if the strain relaxation mechanism of the multiphase film was due to the gradient in thickness, several multiphase Bi-Fe-O films, with constant thickness (35–500 nm), were grown and compared to the single phase BiFeO₃ film with a gradual change in thickness (see Fig. 4a). The

change of out-of plane lattice parameter with thickness was obtained from the pure BiFeO₃ film with thickness gradient grown at 20 mTorr and the multiphase Bi-Fe-O films with constant thickness grown at 5 mTorr (see Fig. 4a). Both pure and multiphase films with 35 nm thickness showed a high degree of

ary between BiFeO₃ and Fe₂O₃, lower the out-of-plane strain in the film. Therefore, the formation of α -Fe₂O₃ by evaporation of the more volatile Bi metal at relatively low oxygen partial pressure enhances the relaxation of the compressive stress in BiFeO₃. The relaxation is accelerated as the α -Fe₂O₃ volume fraction increases.

The existence of secondary phases also affects the magnetic properties of the films. We recently reported the dependence of the magnetic properties on the formation of Fe₂O₃ phases as controlled by the oxygen partial pressure during growth of Bi-Fe-O films.^[15] The saturation magnetization increased to about 80 emu cm⁻³ due to the increase in the volume fraction of γ -Fe₂O₃ in the film. In the present study, we compare the effect of strain and the formation of γ -Fe₂O₃ on the magnetization of BiFeO₃ films. α -Fe₂O₃ and BiFeO₃ are known as canted antiferromagnetic materials at room temperature, and they exhibit weak magnetization of 0.4 emu cm⁻³ and 2 emu cm⁻³ at room temperature, respectively.^[21,22] In contrast, bulk γ -Fe₂O₃ is known to display magnetization of up to 400 emu cm⁻³ at room temperature.^[23] In our previous study of BiFeO₃ films, the increase in volume of the γ -Fe₂O₃ with increasing film thickness showed a great effect on the magnetic properties of the films grown at less than 5 mTorr oxygen pressure.^[15] However, the films grown at 5 mTorr oxygen pressure did not show dramatic increase in magnetization due to a small amount of γ -Fe₂O₃. The magnetization in this sample was controlled by residual strain in the film. Figure 4b shows the change in magnetization with thickness for films grown at 5 mTorr and 20 mTorr oxygen partial pressures. Both pure BiFeO₃ and multiphase Bi-Fe-O films exhibit higher magnetization for the thinner films than for thick films. From the XRD results in Figure 4a, the 35 nm thick film grown at 5 mTorr shows higher strain and higher magnetization (~ 5 emu cm⁻³) (Fig. 4b) than the 50 nm thick BiFeO₃ film grown at 20 mTorr. However, the observed improvement of magnetization is still smaller than the results of Wang et al.,^[5] but it is in agreement with other recent measurements.^[13] This enhanced magnetism could result from the heteroepitaxial strain effect in the canted antiferromagnetic film. The magnetic moments of Fe in BiFeO₃ are ferromagnetically aligned on the (111) plane and antiferromagnetically switched along the [111] direction. Canting of Fe magnetic moment allows weak ferromagnetism in BiFeO₃.^[24,25] Ederer and Spaldin found through density functional theory calculations that weak ferromagnetic moments (0.1 μ_B per unit cell for about 1° canting from the collinear direction) are induced by a structural distortion.^[26]

The BiFeO₃ in-plane lattice parameter, which is reduced by the compressive stress from the SrTiO₃ substrate, results in elongation of the out-of-plane lattice parameter. This strain gives rise to enhancement of magnetization.^[5,13] As the thickness increases, this strain is relaxed and the magnetization is expected to decrease. Since the multiphase BiFeO₃ films have higher strain relaxation due to the formation of α -Fe₂O₃ domains, the magnetization in these films is expected to decrease faster than for pure BiFeO₃ films with increasing thickness. However, this reduction of magnetization is partially compensated by the nucleation of γ -Fe₂O₃. The saturation magnetiza-

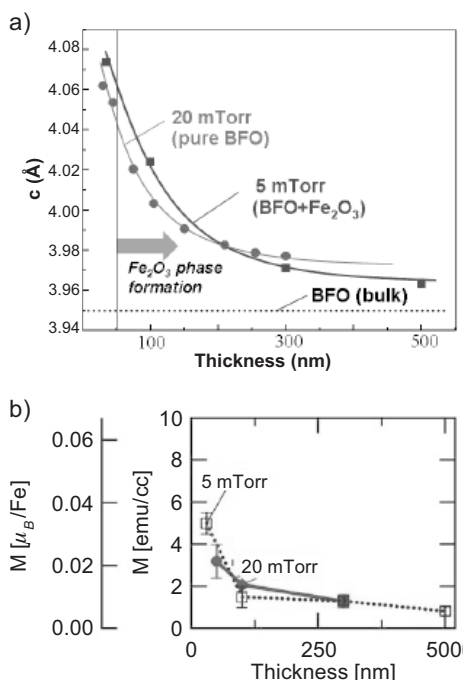


Figure 4. a) Out-of-plane lattice parameters in pure BiFeO₃ (thickness gradient) and BiFeO₃ with secondary phases (constant thickness) as a function of film thickness. b) Room temperature saturation magnetization (emu cm⁻³) of Bi-Fe-O films as a function of thickness for films grown at 5 mTorr and 20 mTorr.

strain. As the film thickness increases from 30 to 300 nm, the out-of-plane lattice parameter of the pure BiFeO₃ film gradually decreases from 0.406 to 0.398 nm. However, in the multiphase films, the out-of-plane lattice parameter decreases from 0.407 to 0.396 nm with increasing film thickness from 35 to 500 nm. This result confirms that the α -Fe₂O₃ domains that form on the surface region of the film for films of thickness above 50 nm (grown at low oxygen partial pressure) enhance the in-plane relaxation of misfit strain in the BiFeO₃ columns. As a result, the total misfit strain reduction is from 0.51 % (pure BiFeO₃) to 0.25 % (mixture of BiFeO₃ and Fe₂O₃) at the thickness of ~ 300 nm. The observation of a broad peak in the XRD spectra in Figure 3b for thicknesses above ~ 50 nm indicates that the bottom portion of the films under the Fe₂O₃ region (region A) in Figure 1b remains strained. In order to understand the higher degree of strain relaxation in the films with Fe₂O₃, we estimate the change in volume in these regions. A reduction in volume of ~ 19 % by the formation of the Fe₂O₃ phase allows expansion (in plane) of BiFeO₃ (which is under in-plane compressive strain with the substrate). This in-plane expansion, together with the formation of the vertical bound-

tion decreases with increasing oxygen partial pressure up to 20 mTorr and remains constant above this pressure when the films become pure BiFeO₃.

To further enhance the magnetic properties of multiphase Bi-Fe-O film with the columnar structure, we explored the possibility of transforming the α -Fe₂O₃ (antiferromagnetic phase) regions to γ -Fe₂O₃ (ferromagnetic phase).^[27] We have devised a two-step process for this purpose. The first stage is hydrogen reduction to transform α -Fe₂O₃ into Fe₃O₄, and the second stage is oxidation to transform Fe₃O₄ to γ -Fe₂O₃. The reduction was conducted by flowing a mixture gas of Ar and H₂ (10Ar:1H₂) for 1 hour while the film was kept at 300 °C. This was followed by oxidation at 300 °C in oxygen ambient for 1 hour. The change of magnetization after the annealing process is shown in Figure 5a. The annealed film showed increased magnetization (~ 6 emu cm⁻³) due to the increase of the γ -Fe₂O₃ fraction (less than 10%). The magnetic domain image of the annealed multiphase Bi-Fe-O film was acquired using MFM to confirm the existence of magnetic domains (γ -Fe₂O₃) after annealing. Figure 5b shows randomly oriented magnetic domains with zero field that switch in the perpendicular direction under an applied magnetic field (Fig. 5d). Comparing the AFM image in Figure 5c with the MFM image in Figure 5d, we can see that the magnetic domains in the films correspond to the Fe₂O₃ regions. From these results, we conclude that the magnetic properties of the films can be controlled by converting α -Fe₂O₃ into γ -Fe₂O₃ through the described procedure. In fact, we found that the magnetization of the films is directly proportional to the volume fraction of γ -Fe₂O₃ which can be controlled by adjusting the annealing time and the concentration of hydrogen in the gas mixture.

Also, effects of the Fe₂O₃ phase formation and microstructural change on the ferroelectric properties of BiFeO₃ films were studied using piezo force microscopy (PFM). Figure 6a and b show a topographic image and an out-of-plane piezoelectric response image, respectively, of a multiphase BiFeO₃ thin film obtained using PFM at room temperature. Figure 6a shows a columnar structure of BiFeO₃ and Fe₂O₃. Relatively high regions represent BiFeO₃. To obtain the piezoelectric response image, the multiphase BiFeO₃ film (Fig. 6b) and pure BiFeO₃ film (Fig. 6c) were first poled by applying a positive DC bias (+10 V) to a conducting probe while scanning over a 3 × 3 μ m² area. Another poling was then performed with a negative voltage (−10 V) during a scan over a 1 × 1 μ m² area. The PFM image shows both written regions with opposite contrast because of the presence of switching of ferroelectric domains in the film. Comparing switching of domains in the pure BiFeO₃ film (Fig. 6c) to the multiphase Bi-Fe-O film

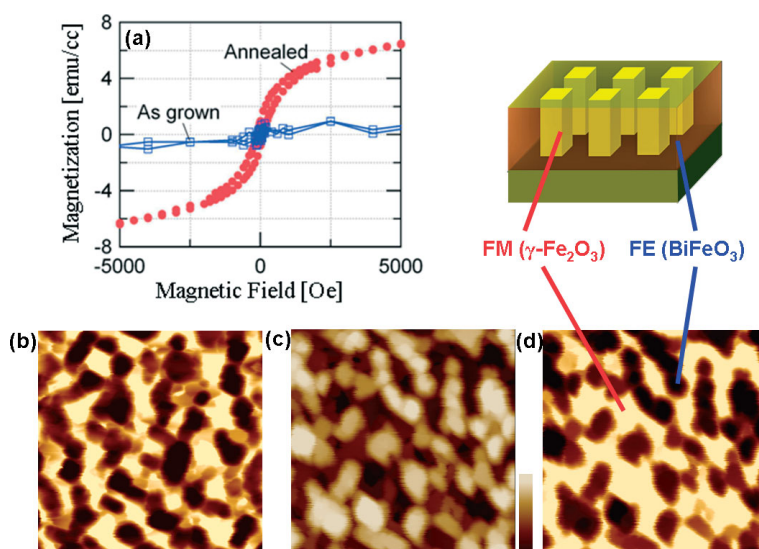


Figure 5. a) Hysteresis loops of as grown and annealed multiphase Bi-Fe-O films. c) AFM topographic image and b) and d) magnetic force microscopy images of an annealed multiphase film with no external field and after magnetizing the film perpendicular to the surface by applying 20 kOe magnetic field, respectively. AFM and MFM images are 4 × 4 μ m scans. The height scale in (c) corresponds to 0–100 nm. The higher (brighter) regions are the BiFeO₃ phase. Schematic is the microstructure of Bi-Fe-O multiferroic nanocomposites.

(Fig. 6b), the multiphase BiFeO₃ film shows enhanced piezo electric response with higher contrast of switching in polarization in the interfacial regions between BiFeO₃ and Fe₂O₃ than the pure BiFeO₃ film. This result is surprising because Fe₂O₃ is not ferroelectric. It is possible that local strains and/or composition gradients across these interfacial regions are responsible for the enhanced piezo electric response. These possibilities are currently under further investigation.

In conclusion, pure BiFeO₃ films were grown on SrTiO₃ with 20 mTorr oxygen pressure. At oxygen pressures below or equal to 5 mTorr, regions containing α -Fe₂O₃ and γ -Fe₂O₃ appear on the top region of the film when the thickness of the film is ~ 50 nm. With continuous deposition, these Fe₂O₃ regions continue to grow to the surface of the film. γ -Fe₂O₃ nucleates in α -Fe₂O₃ with specific orientation forming plate-like structures. The distribution of misfit strain in multiphase Bi-Fe-O film was

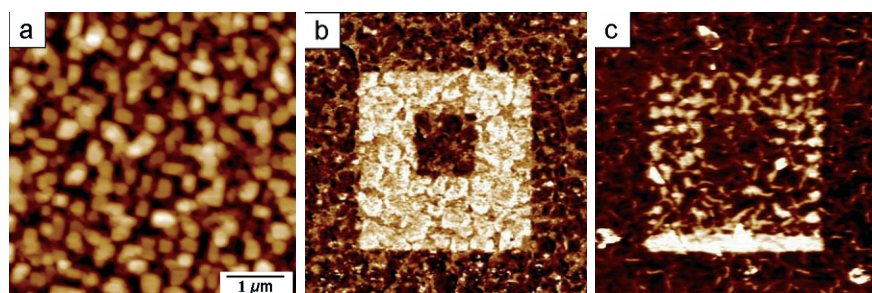


Figure 6. a) AFM topographic image and b) PFM image of ferroelectric domains in multiphase Bi-FeO₃ and c) PFM image of ferroelectric domains in pure BiFeO₃. A DC bias of +10 V was applied within 3 × 3 μ m² area, and then −10 V was applied within 1 × 1 μ m² area in the piezo force microscopy images.

compared to pure BiFeO₃ film, and a strain relaxation mechanism was suggested. The formation of α -Fe₂O₃ prevented the relaxation of the misfit strain in the BiFeO₃ regions below α -Fe₂O₃ columns. The α -Fe₂O₃, however, assisted in the relaxation of strain in the BiFeO₃ columns between α -Fe₂O₃. Preliminary studies show that this misfit strain accommodation caused by formation of α -Fe₂O₃ significantly enhances the piezo electric properties ($d_{33} \approx 70$ pm V⁻¹) and electrical polarization of BiFeO₃ which increased from ~ 2 to 70 μ C cm⁻² (these results will be reported elsewhere).

The magnetization of Bi-Fe-O films is slightly (~ 5 emu cm⁻³) enhanced by strain. However, the large increase in magnetization (of up to ~ 80 emu cm⁻³) in BiFeO₃ films is directly proportional to the volume fraction of γ -Fe₂O₃. We also demonstrated that transformation of α -Fe₂O₃ to γ -Fe₂O₃ is possible by a reduction and oxidation process. This process can be used to increase the magnetization in Bi-Fe-O films. Our results show the possibility of tuning the microstructure and the fraction of the three phases in the Bi-Fe-O system. We have demonstrated that multiferroic nanocomposites with separated columnar structure of ferroelectric and ferromagnetic domains can be achieved by controlling the deposition oxygen pressure, and the properties of the magnetic domains can be tailored to applications through an annealing procedure.

Experimental

Bi-Fe-O thin films with constant thickness (35–500 nm) and with a thickness gradient were deposited on SrTiO₃ (001) substrates at a temperature of 650 °C by PLD. We ablated a stoichiometric BiFeO₃ target with a KrF excimer laser ($\lambda = 248$ nm) with a typical fluence of 2 J cm⁻². The substrates were preheated to 650 °C before deposition, and the deposition rate was ≈ 6 nm min⁻¹. To investigate the multiphase formation, the oxygen partial pressure was varied in the range of 0.1 to 20 mTorr. We also examined the evolution of the crystal structure in films as a function of thickness ranging from 35 to 500 nm, all grown at a constant oxygen partial pressure (5 mTorr). Scanning X-ray microdiffraction (using a D8 DISCOVER with GADDS for combinatorial screening by Bruker-AXS), and EDAX energy dispersive X-ray spectroscopy (EDS) in a JEOL 2100F field emission transmission electron microscope (TEM) were used for identifying the secondary phases. The structural properties of the films were studied by TEM. TEM images and selected area diffraction (SAD) patterns of the films were obtained with a JEOL 4000-FX TEM operated at an accelerating voltage of 300 kV and a JEOL 2100F field emission TEM operated at an accelerating voltage of 200 kV. A MPMS-5 superconducting quantum interference device (SQUID) magnetometer and Digital Instruments (DI) Dimensions 3000 magnetic force microscopy (MFM) were used to perform magnetic characterization. PFM was performed in contact mode on BiFeO₃/Nb-doped SrTiO₃ structures using Pt-Ir coated tips [28].

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